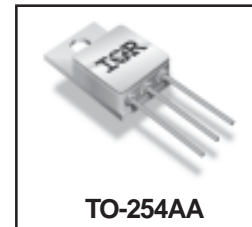


**RADIATION HARDENED
 POWER MOSFET
 THRU-HOLE (TO-254AA)**

**IRHM7150
 JANSR2N7268
 100V, N-CHANNEL
 REF: MIL-PRF-19500/603
 RAD Hard™ HEXFET® TECHNOLOGY**

Product Summary

Part Number	Radiation Level	RDS(on)	Id	QPL Part Number
IRHM7150	100K Rads (Si)	0.065Ω	34A	JANSR2N7268
IRHM3150	300K Rads (Si)	0.065Ω	34A	JANSF2N7268
IRHM4150	500K Rads (Si)	0.065Ω	34A	JANSF2N7268
IRHM8150	1000K Rads (Si)	0.065Ω	34A	JANSH2N7268



International Rectifier's RADHard™ HEXFET® technology provides high performance power MOSFETs for space applications. This technology has over a decade of proven performance and reliability in satellite applications. These devices have been characterized for both Total Dose and Single Event Effects (SEE). The combination of low Rds(on) and low gate charge reduces the power losses in switching applications such as DC to DC converters and motor control. These devices retain all of the well established advantages of MOSFETs such as voltage control, fast switching, ease of paralleling and temperature stability of electrical parameters.

Features:

- Single Event Effect (SEE) Hardened
- Low RDS(on)
- Low Total Gate Charge
- Simple Drive Requirements
- Ease of Paralleling
- Hermetically Sealed
- Ceramic Eyelets
- Light Weight

Absolute Maximum Ratings

Pre-Irradiation

	Parameter		Units
I_D @ $V_{GS} = 12V, T_C = 25^\circ C$	Continuous Drain Current	34	A
I_D @ $V_{GS} = 12V, T_C = 100^\circ C$	Continuous Drain Current	21	
I_{DM}	Pulsed Drain Current ①	136	
P_D @ $T_C = 25^\circ C$	Max. Power Dissipation	150	W
	Linear Derating Factor	1.2	W/°C
V_{GS}	Gate-to-Source Voltage	±20	V
EAS	Single Pulse Avalanche Energy ②	500	mJ
I_{AR}	Avalanche Current ①	34	A
EAR	Repetitive Avalanche Energy ①	15	mJ
dv/dt	Peak Diode Recovery dv/dt ③	5.5	V/ns
T_J	Operating Junction	-55 to 150	°C
T_{STG}	Storage Temperature Range		
	Lead Temperature	300 (0.063 in. (1.6mm) from case for 10s)	
	Weight	9.3 (Typical)	

For footnotes refer to the last page

Electrical Characteristics @ T_j = 25°C (Unless Otherwise Specified)

	Parameter	Min	Typ	Max	Units	Test Conditions
BV _{DSS}	Drain-to-Source Breakdown Voltage	100	—	—	V	V _{GS} = 0 V, I _D = 1.0mA
ΔBV _{DSS} /ΔT _J	Temperature Coefficient of Breakdown Voltage	—	0.13	—	V/°C	Reference to 25°C, I _D = 1.0mA
R _{DS(on)}	Static Drain-to-Source On-State Resistance	—	—	0.065 0.076	Ω	V _{GS} = 12V, I _D = 21A V _{GS} = 12V, I _D = 34A ④
V _{GS(th)}	Gate Threshold Voltage	2.0	—	4.0	V	V _{DS} = V _{GS} , I _D = 1.0mA
g _{fs}	Forward Transconductance	8.0	—	—	S (r̄)	V _{DS} > 15V, I _{DS} = 21A ④
I _{DSS}	Zero Gate Voltage Drain Current	—	—	25 250	μA	V _{DS} = 80V, V _{GS} = 0V V _{DS} = 80V V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Leakage Forward	—	—	100	nA	V _{GS} = 20V
I _{GSS}	Gate-to-Source Leakage Reverse	—	—	-100	nA	V _{GS} = -20V
Q _g	Total Gate Charge	—	—	160	nC	V _{GS} = 12V, I _D = 34A V _{DS} = 50V
Q _{gs}	Gate-to-Source Charge	—	—	35	nC	
Q _{gd}	Gate-to-Drain ('Miller') Charge	—	—	65	nC	
t _{d(on)}	Turn-On Delay Time	—	—	45	ns	V _{DD} = 50V, I _D = 14A, V _{GS} = 12V, R _G = 2.35Ω
t _r	Rise Time	—	—	190		
t _{d(off)}	Turn-Off Delay Time	—	—	170		
t _f	Fall Time	—	—	130		
LS + LD	Total Inductance	—	6.8	—	nH	Measured from drain lead (6mm/0.25in. from package) to source lead (6mm/0.25in. from package)
C _{iss}	Input Capacitance	—	4300	—	pF	V _{GS} = 0V, V _{DS} = 25V f = 1.0MHz
C _{oss}	Output Capacitance	—	1200	—		
C _{rss}	Reverse Transfer Capacitance	—	200	—		

Source-Drain Diode Ratings and Characteristics

	Parameter	Min	Typ	Max	Units	Test Conditions
I _S	Continuous Source Current (Body Diode)	—	—	34	A	
I _{SM}	Pulse Source Current (Body Diode) ①	—	—	136		
V _{SD}	Diode Forward Voltage	—	—	1.4	V	T _j = 25°C, I _S = 34A, V _{GS} = 0V ④
t _{rr}	Reverse Recovery Time	—	—	570	ns	T _j = 25°C, I _F = 34A, di/dt ≤ 100A/μs V _{DD} ≤ 50V ④
Q _{RR}	Reverse Recovery Charge	—	—	5.8	μC	
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by LS + LD.				

Thermal Resistance

	Parameter	Min	Typ	Max	Units	Test Conditions
R _{thJC}	Junction-to-Case	—	—	0.83	°C/W	Typical socket mount
R _{thCS}	Case-to-sink	—	0.21	—		
R _{thJA}	Junction-to-Ambient	—	—	48		

Note: Corresponding Spice and Saber models are available on the International Rectifier Website.

For footnotes refer to the last page

Radiation Characteristics

IRHM7150, JANSR2N7268

International Rectifier Radiation Hardened MOSFETs are tested to verify their radiation hardness capability. The hardness assurance program at International Rectifier is comprised of two radiation environments. Every manufacturing lot is tested for total ionizing dose (per notes 5 and 6) using the TO-3 package. Both pre- and post-irradiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison.

Table 1. Electrical Characteristics @ Tj = 25°C, Post Total Dose Irradiation ⑤⑥

	Parameter	100K Rads(Si) ¹		300 - 1000K Rads (Si) ²		Units	Test Conditions
		Min	Max	Min	Max		
BV _{DSS}	Drain-to-Source Breakdown Voltage	100	—	100	—	V	V _{GS} = 0V, I _D = 1.0mA
V _{GS(th)}	Gate Threshold Voltage ④	2.0	4.0	1.25	4.5		V _{GS} = V _{DS} , I _D = 1.0mA
I _{GS}	Gate-to-Source Leakage Forward	—	100	—	100	nA	V _{GS} = 20V
I _{GS}	Gate-to-Source Leakage Reverse	—	-100	—	-100		V _{GS} = -20 V
I _{DSS}	Zero Gate Voltage Drain Current	—	25	—	50	μA	V _{DS} =80V, V _{GS} =0V
R _{DS(on)}	Static Drain-to-Source ④ On-State Resistance (TO-3)	—	0.065	—	0.09	Ω	V _{GS} = 12V, I _D =21A
R _{DS(on)}	Static Drain-to-Source ④ On-State Resistance (TO-254AA)	—	0.065	—	0.09	Ω	V _{GS} = 12V, I _D =21A
V _{SD}	Diode Forward Voltage ④	—	1.4	—	1.4	V	V _{GS} = 0V, I _S = 34A

1. Part number IRHM7150 (JANSR2N7268)

2. Part numbers IRHM3150 (JANSF2N7268), IRHM4150 (JANSJ2N7268) and IRHM8150 (JANSH2N7268)

International Rectifier radiation hardened MOSFETs have been characterized in heavy ion environment for Single Event Effects (SEE). Single Event Effects characterization is illustrated in Fig. a and Table 2.

Table 2. Single Event Effect Safe Operating Area

Ion	LET (MeV/(mg/cm ²))	Energy (MeV)	Range (μm)	V _{DS} (V)				
				@V _{GS} =0V	@V _{GS} =-5V	@V _{GS} =-10V	@V _{GS} =-15V	@V _{GS} =-20V
Cu	28	285	43	100	100	100	80	60
Br	36.8	305	39	100	90	70	50	—

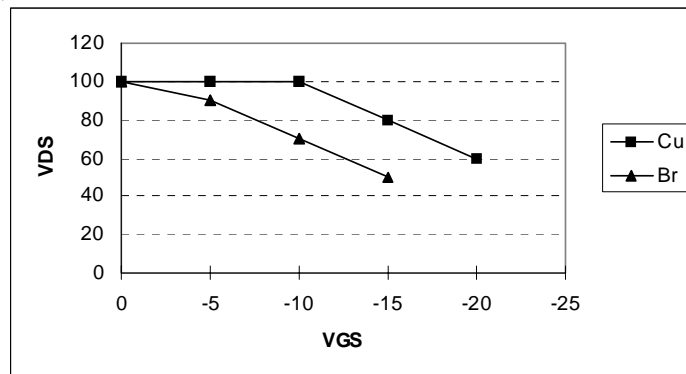


Fig a. Single Event Effect, Safe Operating Area

For footnotes refer to the last page

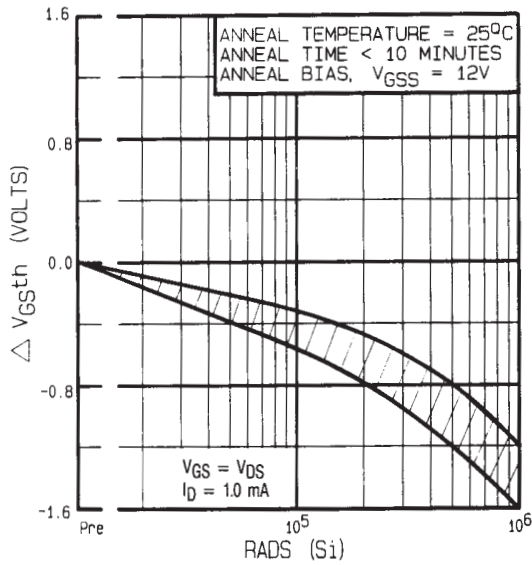


Fig 1. Typical Response of Gate Threshold Voltage Vs. Total Dose Exposure

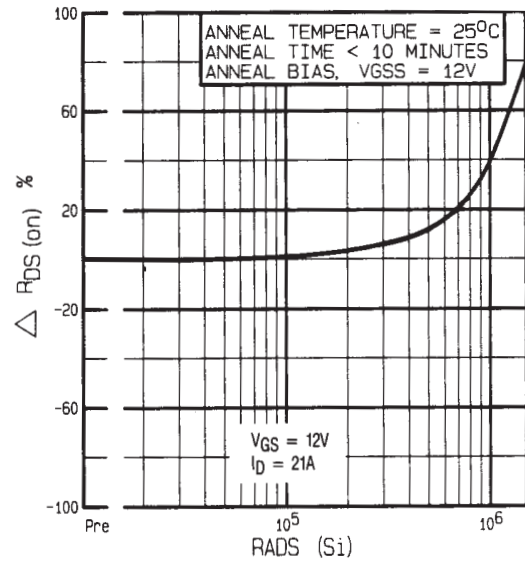


Fig 2. Typical Response of On-State Resistance Vs. Total Dose Exposure

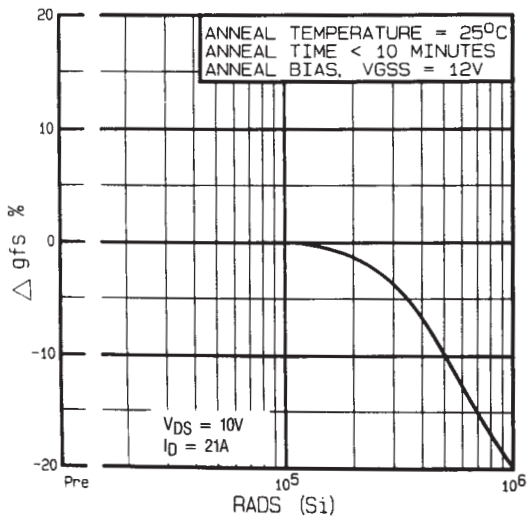


Fig 3. Typical Response of Transconductance Vs. Total Dose Exposure

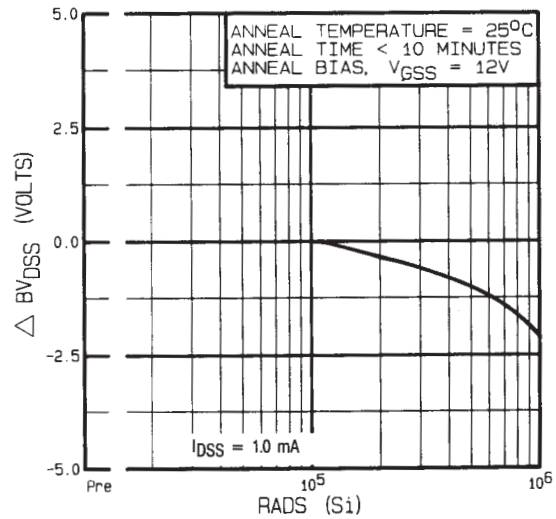


Fig 4. Typical Response of Drain to Source Breakdown Vs. Total Dose Exposure

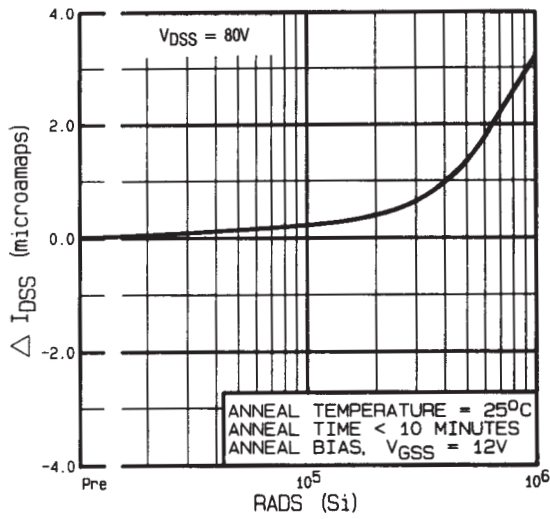


Fig 5. Typical Zero Gate Voltage Drain Current Vs. Total Dose Exposure

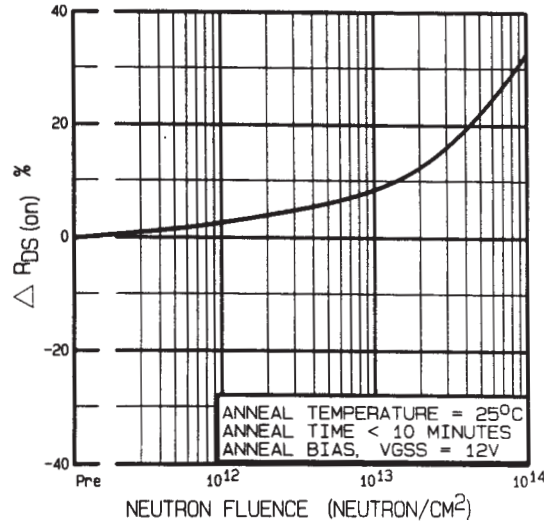


Fig 6. Typical On-State Resistance Vs. Neutron Fluence Level

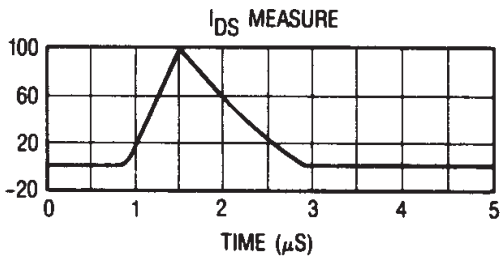
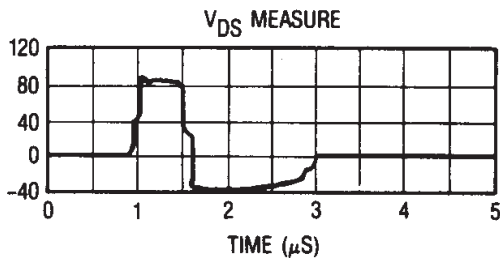


Fig 7. Typical Transient Response of Rad Hard HEXFET During 1×10^{12} Rad (Si)/Sec Exposure

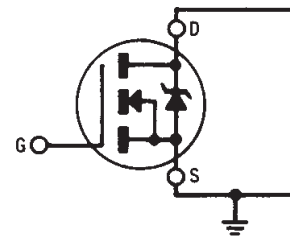


Fig 8a. Gate Stress of V_{GSS} Equals 12 Volts During Radiation

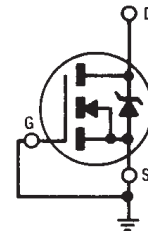


Fig 8b. V_{DSS} Stress Equals 80% of $B_{V_{DS}}$ During Radiation

Note: Bias Conditions during radiation: $V_{GS} = 12 \text{ Vdc}$, $V_{DS} = 0 \text{ Vdc}$

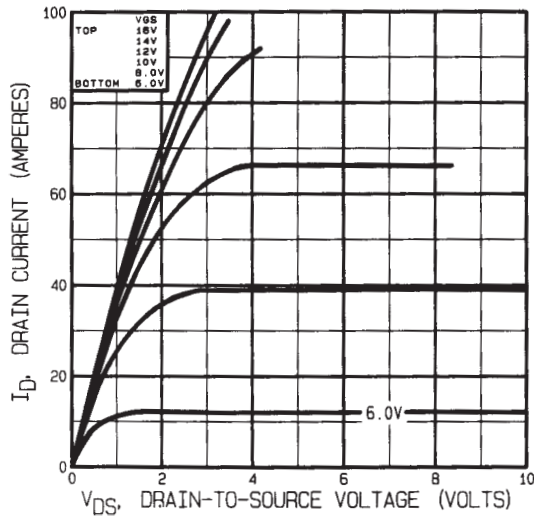


Fig 9. Typical Output Characteristics Pre-Irradiation

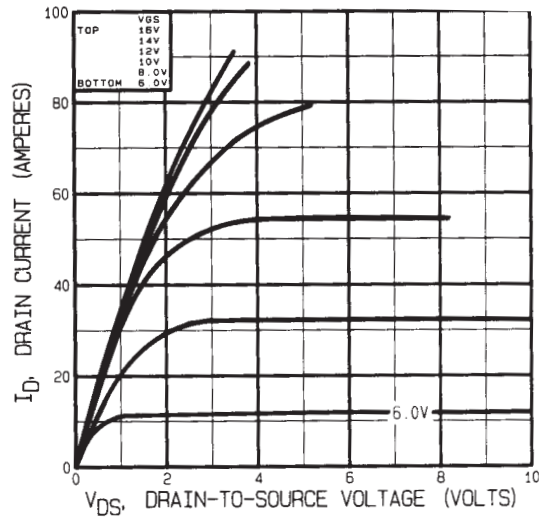


Fig 10. Typical Output Characteristics Post-Irradiation 100K Rads (Si)

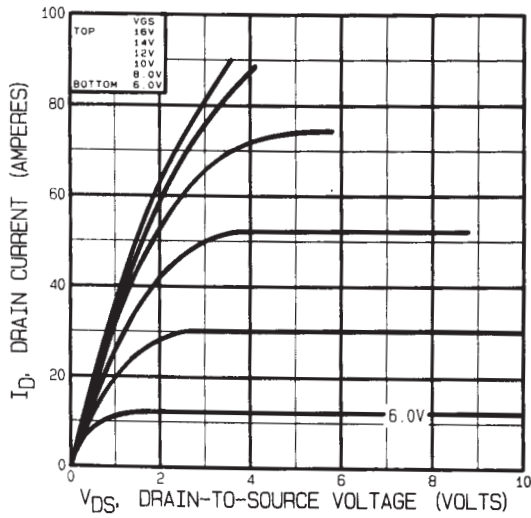


Fig 11. Typical Output Characteristics Post-Irradiation 300K Rads (Si)

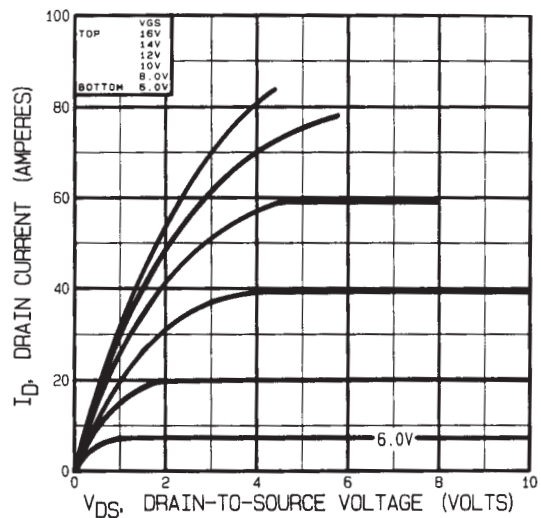


Fig 12. Typical Output Characteristics Post-Irradiation 1 Mega Rads (Si)

Radiation Characteristics

IRHM7150, JANSR2N7268

Note: Bias Conditions during radiation: $V_{GS} = 0$ Vdc, $V_{DS} = 80$ Vdc

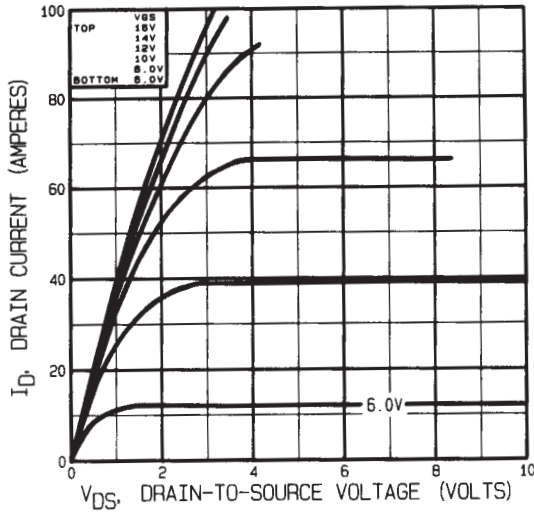


Fig 13. Typical Output Characteristics Pre-Irradiation

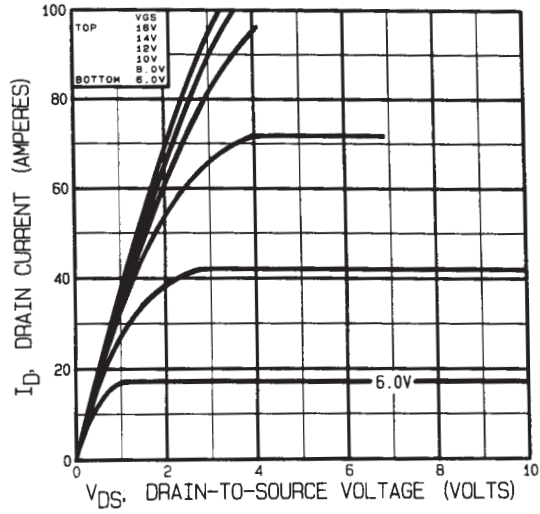


Fig 14. Typical Output Characteristics Post-Irradiation 100K Rads (Si)

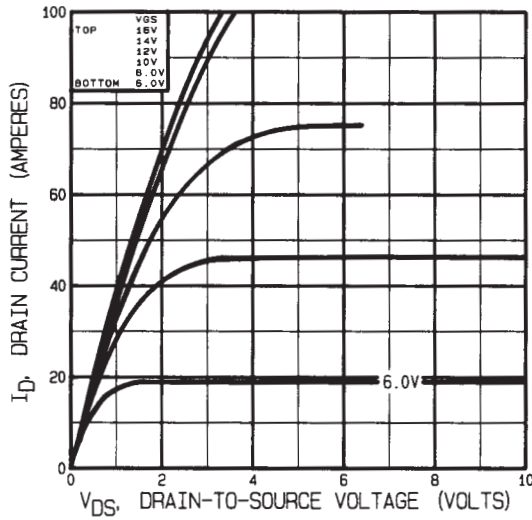


Fig 15. Typical Output Characteristics Post-Irradiation 300K Rads (Si)

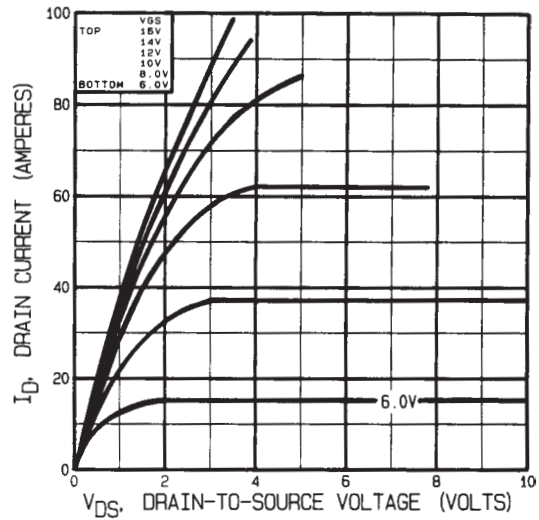


Fig 16. Typical Output Characteristics Post-Irradiation 1 Mega Rads (Si)

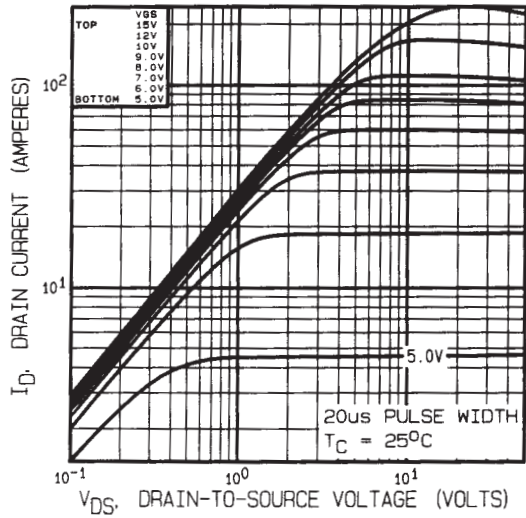


Fig 17. Typical Output Characteristics

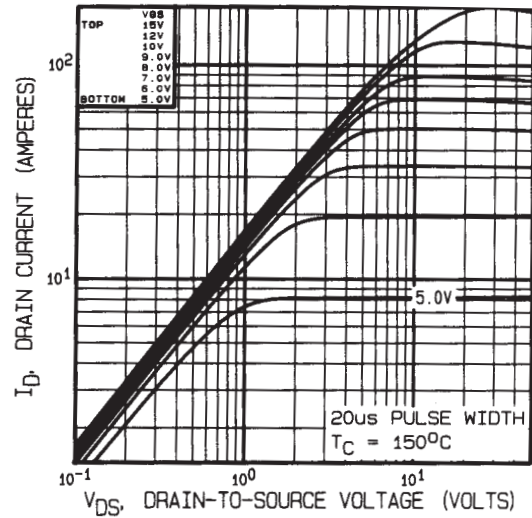


Fig 18. Typical Output Characteristics

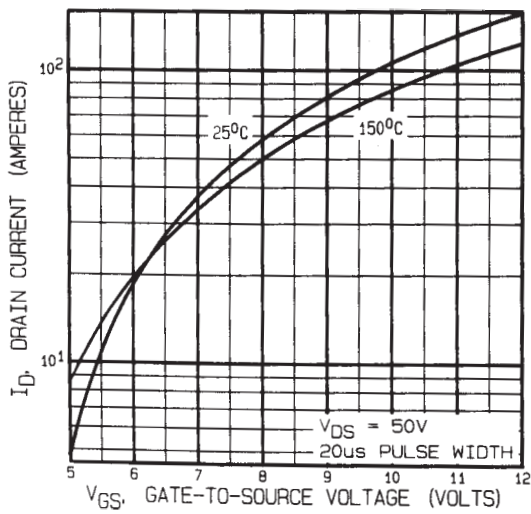


Fig 19. Typical Transfer Characteristics

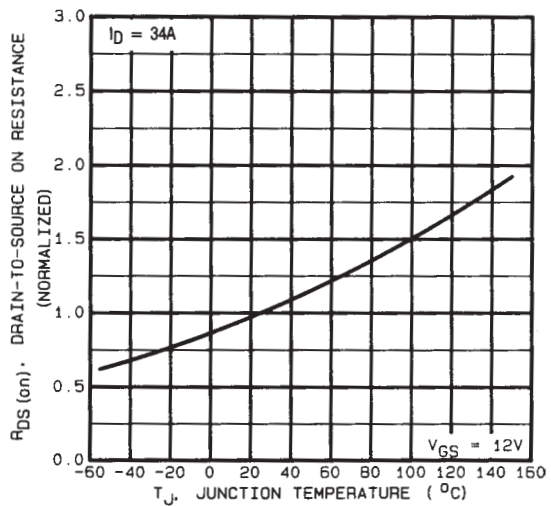


Fig 20. Normalized On-Resistance Vs. Temperature

Pre-Irradiation

IRHM7150, JANSR2N7268

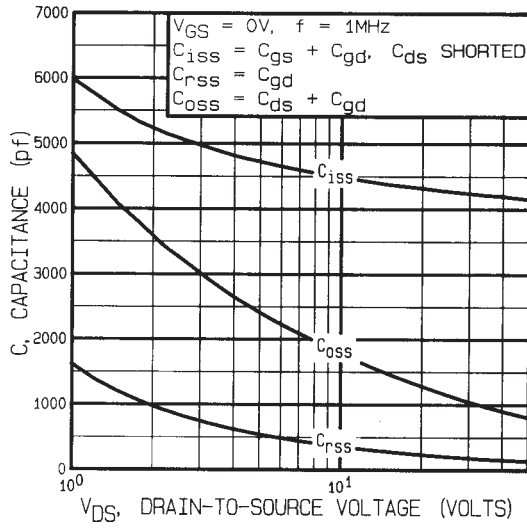


Fig 21. Typical Capacitance Vs. Drain-to-Source Voltage

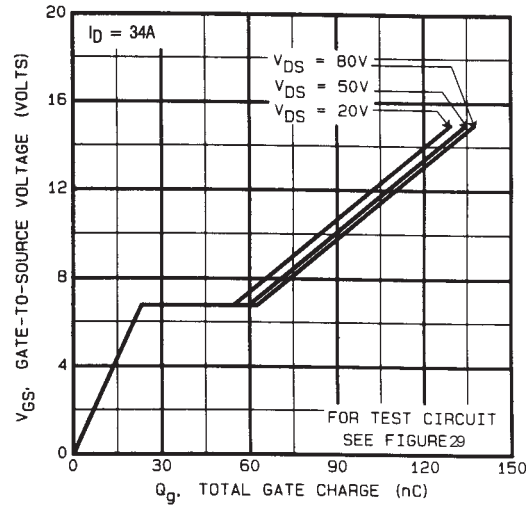


Fig 22. Typical Gate Charge Vs. Gate-to-Source Voltage

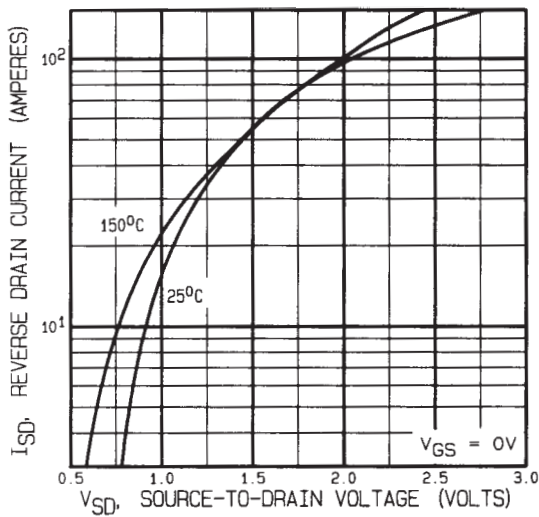


Fig 23. Typical Source-Drain Diode Forward Voltage

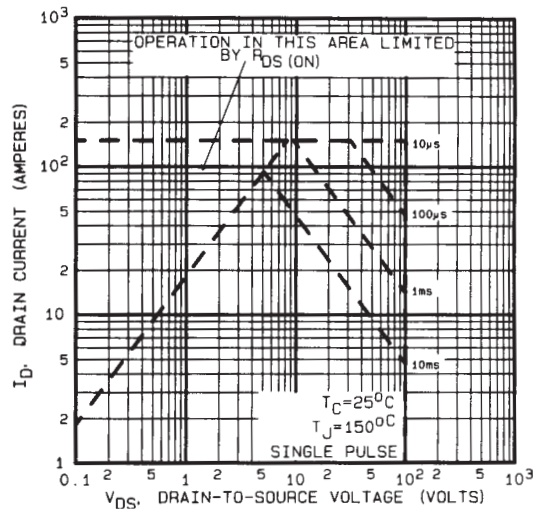


Fig 24. Maximum Safe Operating Area

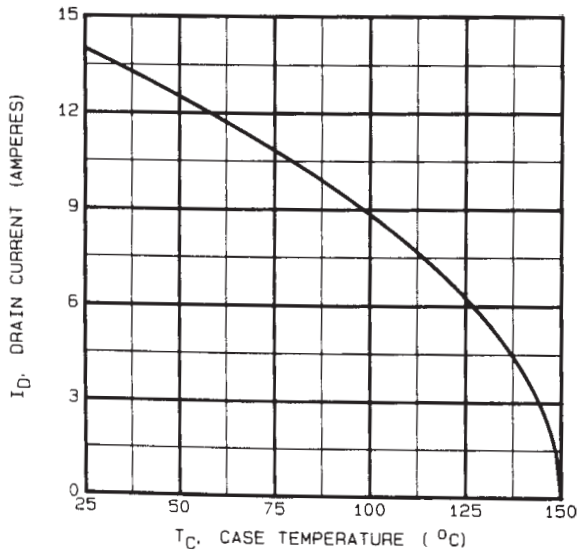


Fig 25. Maximum Drain Current Vs. Case Temperature

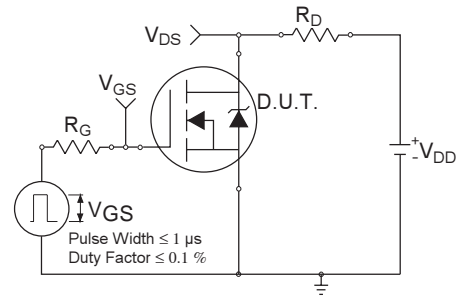


Fig 26a. Switching Time Test Circuit

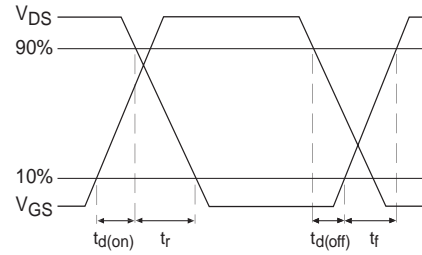


Fig 26b. Switching Time Waveforms

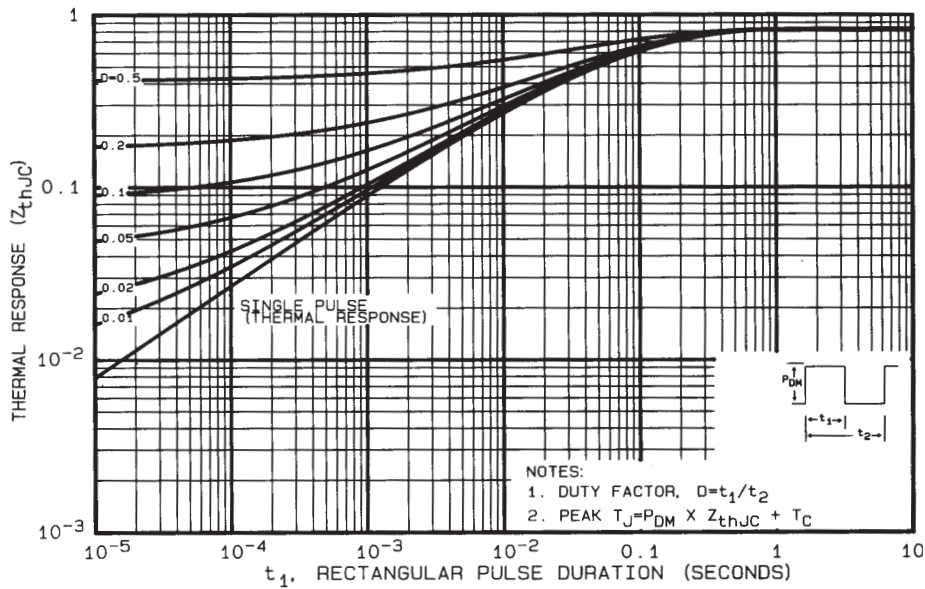


Fig 27. Maximum Effective Transient Thermal Impedance, Junction-to-Case

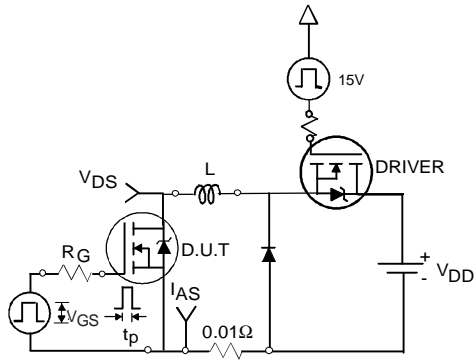


Fig 28a. Unclamped Inductive Test Circuit

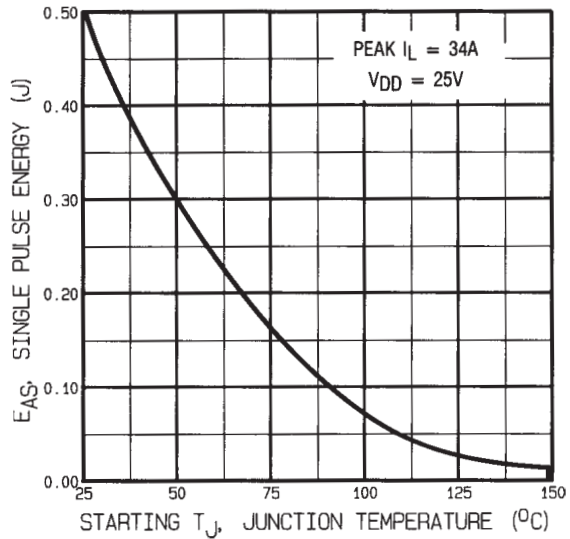


Fig 28c. Maximum Avalanche Energy Vs. Drain Current

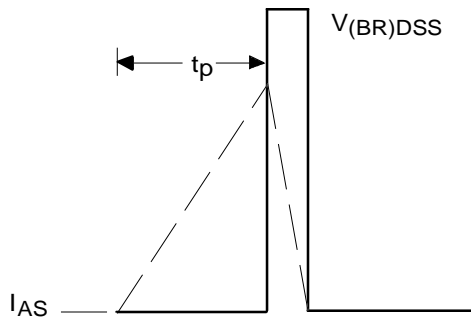


Fig 28b. Unclamped Inductive Waveforms

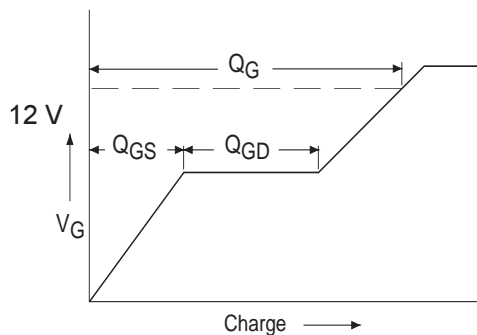


Fig 29a. Basic Gate Charge Waveform

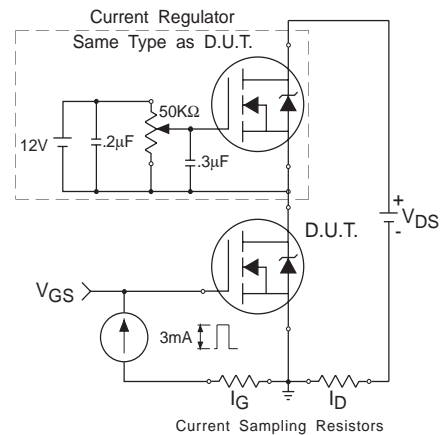


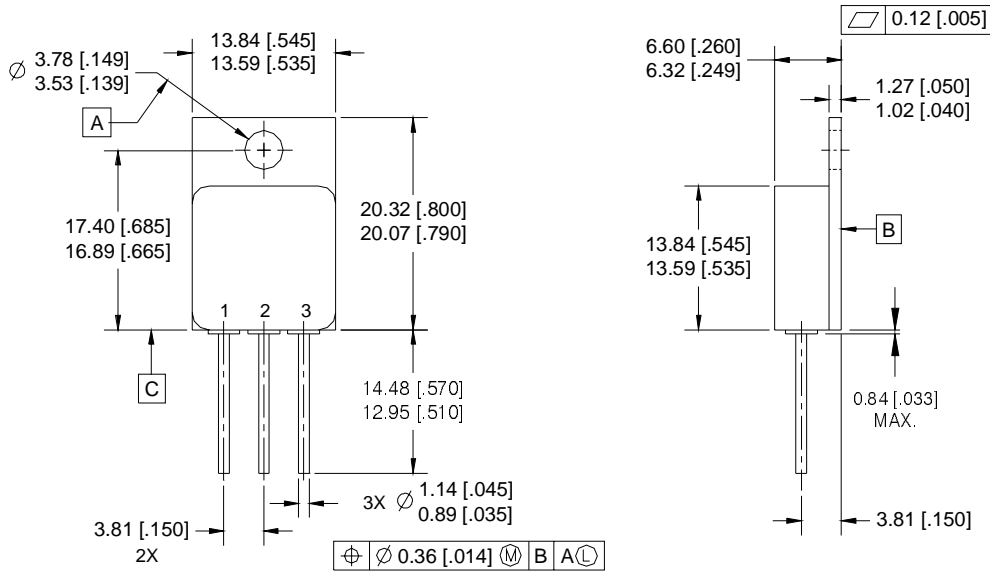
Fig 29b. Gate Charge Test Circuit

Foot Notes:

- ① Repetitive Rating; Pulse width limited by maximum junction temperature.
- ② $V_{DD} = 25V$, starting $T_J = 25^\circ C$, $L = 0.86mH$
Peak $I_L = 26A$, $V_{GS} = 12V$
- ③ $I_{SD} \leq 26A$, $di/dt \leq 190A/\mu s$,
 $V_{DD} \leq 100V$, $T_J \leq 150^\circ C$

- ④ Pulse width $\leq 300 \mu s$; Duty Cycle $\leq 2\%$
- ⑤ **Total Dose Irradiation with V_{GS} Bias.**
12 volt V_{GS} applied and $V_{DS} = 0$ during irradiation per MIL-STD-750, method 1019, condition A.
- ⑥ **Total Dose Irradiation with V_{DS} Bias.**
80 volt V_{DS} applied and $V_{GS} = 0$ during irradiation per MIL-STD-750, method 1019, condition A.

Case Outline and Dimensions — Low-Ohmic TO-254AA



NOTES:

- 1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
- 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- 3. CONTROLLING DIMENSION: INCH.
- 4. CONFORMS TO JEDEC OUTLINE TO-254AA.

PIN ASSIGNMENTS

- 1 = DRAIN
- 2 = SOURCE
- 3 = GATE

CAUTION

BERYLLIA WARNING PER MIL-PRF-19500

Packages containing beryllia shall not be ground, sandblasted, machined or have other operations performed on them which will produce beryllia or beryllium dust. Furthermore, beryllium oxide packages shall not be placed in acids that will produce fumes containing beryllium.



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IR LEOMINSTER : 205 Crawford St., Leominster, Massachusetts 01453, USA Tel: (978) 534-5776
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Data and specifications subject to change without notice. 05/2006